PCN Numl	ber:	2024	401	16004.2		PCN D	ate:	January 16, 2024		
Title:	Qualification of	of RFA	λB u	B using qualified Process Technology, Die Revision, and additional						
ritie:	Assembly BON	1 opti	io ns	ons for the ULQ2003AQDRQ1 device						
Customer	Contact:		Ch	ange Management t	team	Dept:		Quality Services		
Proposed	1 st Ship Date:		Jul	16, 2024	Estima			Feb 16, 2024*		
				<u> </u>		Availabi		·		
*Sample r	equests recei	ved a	a fte	r February 16, 20	24 will 1	not be	suppo	orted.		
Change Ty	/pe:									
Assemb	ly Site		☑ Design				Wafer Bump Material			
⊠ Assemb	ly Process		☐ Data Sheet				Wafer Bump Process			
	ly Materials			Part number char	ige		Wafe	er Fab Site		
Mechan	ical Specification	on		Test Site			Wafe	er Fab Materials		
☑ Packing/Shipping/Labeling				☐ Test Process			Wafer Fab Process			
_		•					•			
				PCN Deta	ils					

Description of Change:

Texas Instruments is pleased to announce the addition of RFAB using the TIB qualified process technology and additional Assembly BOM options for the device listed below.

С	urrent Fab Si	te	Additional Fab Site				
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter		
SFAB	JI1	150 mm	RFAB	TIB	300 mm		

The die was also changed as a result of the process change.

Additionally, there will be a BOM options introduced for these devices:

What	Current	Additional
Bond Wire composition, diameter	Au, 1.15 mil	Cu, 1.0 mil
Wafer Thickness	10.5 mils	7.5 mils

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
⊠ No Change	⊠ No Change	☑ No Change	⊠ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:			
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
RFAB	RFB	USA	Richardson

Die Rev:

Current	New
Die Rev [2P]	Die Rev [2P]
С	A

Sample product shipping label (not actual product label)



Product Affected:

ULQ2003AQDRQ1

For alternate parts with similar or improved performance, please visit the product page on $\overline{\text{TI.com}}$

Automotive New Product Qualification Summary (As per AEC-Q100 Rev. H and JEDEC Guidelines)

Product Attributes

Attributes	Qual Device:	QBS Package, Process Reference:		
	ULQ2003AQDRQ1	<u>MC33063AQDRQ1</u>		
Automotive Grade Level	Grade 1	Grade 1		
Operating Temp Range (C)	-40 to 125	-40 to 125		
Product Function	Power Management	Power Management		
Wafer Fab Supplier	RFAB	RFAB		
Assembly Site	FMX	FMX		
Package Group	SOIC	SOIC		
Package Designator	D	D		
Pin Count	16	8		

- QBS: Qual By Similarity
- Qual Device ULQ2003AQDRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ULQ2003AQDRQ1	QBS Package, Process Reference: <u>MC33063AQDRQ1</u>
Test Group	A - Acce	lerated Environment Stre	ss Test	S					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	No Fails	No Fails
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	1/45/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0	3/135/0
Test Group	B - Acce	lerated Lifetime Simulation	on Tests						
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	3/231/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0
Test Group	C - Pack	age Assembly Integrity T	ests						
									ODS Backage
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>ULQ2003AQDRQ1</u>	QBS Package, Process Reference: MC33063AQDRQ1
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	1/15/0
SD	С3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100							
Test Group		and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0
	D - Die F			10		Cpk>1.67	-	1/10/0	3/30/0
ЕМ	D - Die F	and B108		-		Cpk>1.67	-	1/10/0 Completed Per Process Technology Requirements	3/30/0 Completed Per Process Technology Requirements
EM		and B108 abrication Reliability Test	ts		Dimensions	Cpk>1.67	-	Completed Per Process Technology	Completed Per Process Technology
	D1	and B108 abrication Reliability Test JESD61	ts -	-	Dimensions Electromigration Time Dependent Dielectric	-	-	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology
TDDB	D1	and B108 abrication Reliability Test JESD61 JESD35	ts -	-	Electromigration Time Dependent Dielectric Breakdown Hot Carrier	-		Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology
TDDB	D1 D2 D3	and B108 abrication Reliability Test JESD61 JESD35 JESD60 & 28	-	-	Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Bias Temperature	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology
TDDB HCI BTI SM	D1 D2 D3 D4 D5	and B108 abrication Reliability Test JESD61 JESD35 JESD60 & 28	-		Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Bias Temperature Instability	-	-	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements
TDDB HCI BTI SM	D1 D2 D3 D4 D5	and B108 abrication Reliability Test JESD61 JESD35 JESD60 & 28	-		Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Bias Temperature Instability	-	-	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements
TDDB HCI BTI SM Test Group	D1 D2 D3 D4 D5 E-Elect	and B108 abrication Reliability Test JESD61 JESD35 JESD60 & 28 - rical Verification Tests	-	-	Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Bias Temperature Instability Stress Migration	-	2000	Completed Per Process Technology Requirements Requirements	Completed Per Process Technology Requirements

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ULQ2003AQDRQ1	QBS Package, Process Reference: <u>MC33063AQDRQ1</u>
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0
Additional T	ests								

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Orderable Part Numbers

The following table contains a list of all TI Orderable Part Numbers (OPNs) released by this qualification per Product Qualification Family definition (AEC Q100 Appendix 1). Group E results shown above cover all part numbers listed here.

ULQ2003AQDRQ1

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2205-004

Automotive New Product Qualification Summary (As per AEC-Q100 Rev. H and JEDEC Guidelines)

Product Attributes

Attributes	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:	
Attributes	ULQ2003AQDRQ1	MC33063AQDRQ1	<u>OPA2991QDRQ1</u>	ULQ2003AQDRQ1	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	
Product Function	Power Management	Power Management	Signal Chain	Power Management	
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	
Assembly Site	MLA	FMX	MLA	FMX	
Package Group	SOIC	SOIC	SOIC	SOIC	
Package Designator	D	D	D	D	
Pin Count	16	8	8	16	

- QBS: Qual By Similarity
- Qual Device ULQ2003AQDRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>ULQ2003AQDRQ1</u>	QBS Process Reference: MC33063AQDRQ1	QBS Package Reference: <u>OPA2991QDRQ1</u>	QBS Product Reference: <u>ULQ2003AQDRQ1</u>
Test Group	A - Acce	elerated Enviror	ment St	ress Tes	sts						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	-	No Fails	-	No Fails	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-	3/231/0	-
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0	-	-	-
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-	3/231/0	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	1/5/0	-
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	1/45/0	-	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	-	3/135/0	-
Test Group	B - Acce	elerated Lifetime	e Simula	tion Test	ts						
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	-	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>ULQ2003AQDRQ1</u>	QBS Process Reference: MC33063AQDRQ1	QBS Package Reference: <u>OPA2991QDRQ1</u>	QBS Product Reference: <u>ULQ2003AQDRQ1</u>
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	150C	300 Hours	-	-	-	3/231/0
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-	-
Test Group	C - Pack	age Assembly I	Integrity	Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-	3/90/0	-
SD	C3	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	-	-	-
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-	3/30/0	-
Test Group I	D - Die F	abrication Relia	bility Te	sts							
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Туре	#	Test Spec	Min Lot	SS /	Test Name			Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:
34.			Qty	Lot					MC33063AQDRQ1	OPA2991QDRQ1	ULQ2003AQDRQ1
ВТІ	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verificatio	n Tests								
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	-	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	-	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	3/90/0	3/90/0	3/90/0
Additional T	ests										

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Orderable Part Numbers

The following table contains a list of all TI Orderable Part Numbers (OPNs) released by this qualification per Product Qualification Family definition (AEC Q100 Appendix 1). Group E results shown above cover all part numbers listed here.

ULQ2003AQDRQ1

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2205-003

Automotive New Product Qualification Summary (As per AEC-Q100, Q006 and JEDEC Guidelines)

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: MC33063AQDRQ1					
T	Test Group A – Accelerated Environment Stress Tests												
				3	12	SAM Analysis, T0	Completed	3/66/0					
	PC	A 1	JEDEC J-STD-020; JESD22-A113	3	77	Preconditioning	Level 1- 260C	3/AII/0					
				3	12	SAM Analysis, Post Preconditioning	Completed	3/66/0					

Ту	pe	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: MC33063AQDRQ1		
НА	ST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0		
НА	ST	A2	JEDEC JESD22- A110	3	70	Biased HAST, 130C/85%RH	192 Hours	3/210/0		
				3	1	Cross Section, Post bHAST 192 Hours	Completed	3/3/0		
				3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	3/66/0		
				3	30	Wire Bond Shear, Post bHast 192 Hours	Wires	3/90/0		
				3	30	Bond Pull over Stitch, post bHAST 192 Hours	Wires	3/90/0		
				3	30	Bond Pull over Ball, Post bHAST 192 Hours	Wires	3/90/0		
T	С	A4	JEDEC JESD22- A104	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0		
				3	22	SAM Analysis, Post T/C 500 Cycles	Completed	3/66/0		
Т	С	A4	JEDEC JESD22- A104	3	70	Temperature Cycle, -65/150C	1000 Cycles	3/210/0		
				3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0		
				3	22	SAM Analysis, Post T/C 1000 Cycles	Completed	3/66/0		
				3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/90/0		
				3	30	Bond Pull over Stitch, Post T/C 1000 Cycles	Wires	3/90/0		
			15550 15550	3	30	Bond Pull over Ball, Post T/C 1000 Cycles	Wires	3/90/0		
P.	тс	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	N/A		
P.	тс	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, -40/125C	2000 Cycles	N/A		
нт	ΓSL	A6	JEDEC JESD22- A103	3	45	High Temp Storage Bake 175C	500 Hours	3/135/0		
нт	rsL	A6	JEDEC JESD22- A103	3	44	High Temp Storage Bake 175C	1000 Hours	3/132/0		
				3	1	Cross Section, Post HTSL 1000 Hours	Completed	3/3/0		
Test 0	Test Group C – Package Assembly Integrity Tests									
w	BS	C1	AEC Q100-001	1	30	Wire Bond Shear, Cpk>1.67	Wires	3/90/0		
W	BP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull, Cpk>1.67	Wires	3/90/0		

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

TI Qualification ID: R-2203-095

ZVEI ID: SEM-PW-13, SEM-PW-02, SEM-PW-09, SEM-PA-08, SEM-PA-19, SEM-PA-03, SEM-DE-03, SEM-PW-03

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.